/ Descriptions

TO-252 N MOS N-CHANNEL MOSFET in a TO-252 Plastic Package.

/ Features

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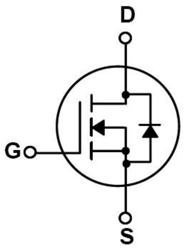
Low gate charge, low crss, fast switching.

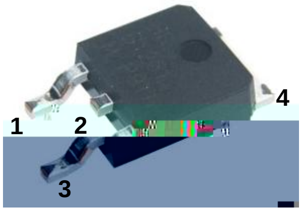
/ Applications

These devices are well suited for power switch circuit of adaptor and charger.

/ Equivalent Circuit



/ Pinning



PIN1 G PIN 2 D PIN 3 S PIN 4 D

/ h_{FE} Classifications & Marking

See Marking Instructions.

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/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	Q_g	I_D=4.0A V_{DS}=350V V_{GS}=10V		15		nC
Gate-to-Source Charge	Q_{gs}			3		nC
Gate-to-Drain Charge	Q_{gd}			6		nC
Continuous Diode Forward Current	I_S				4.0	A
Diode Forward Voltage	V_{SD}	I_s=4.0A V_{GS}=0V $T_{j=}$25			1.4	V
Reverse Recovery Time	t_{rr}	I_f=4.0A T_j=25 di/dt=100A/ s		198		nS
Reverse Recovery Charge	Q_{rr}			770		uC

(Notes):

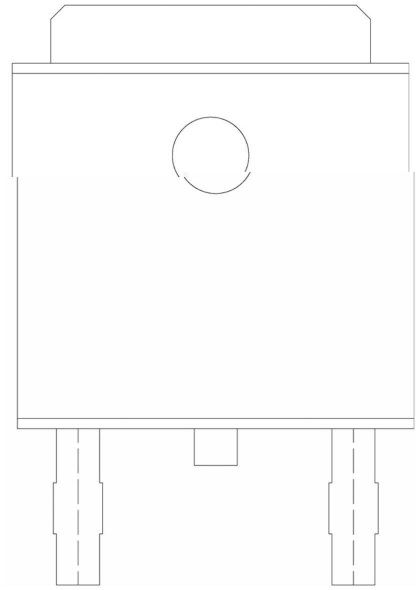
Repetitive rating: Pulse width limited by maximum junction temperature

=25 ,V_{DD}=50V,L=30mH,R_G =25Ω,I_{AS}=4.0A

Starting T_j=25 ,VDD=50V,L=30mH,RG=25 ,I_{AS}=4.0A

≤300μs ≤2
Pulse Test:Pulse width 300 s,Duty cycle 2%

/ Marking Instructions



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Note:

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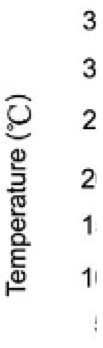

1 25 15
2 245±5
3

/

260±5

/ Packagi

/ REEL

Package Type	

Package Typ

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